

Matthew D McCluskey

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

168
papers

4,940
citations

34
h-index

66
g-index

179
ext. papers

5,347
ext. citations

3
avg, IF

6.06
L-index

#	Paper	IF	Citations
168	Cu ²⁺ and Cu ³⁺ acceptors in β -Ga ₂ O ₃ crystals: A magnetic resonance and optical absorption study. <i>Journal of Applied Physics</i> , 2022 , 131, 065702	2.5	3
167	Persistent Room-Temperature Photodarkening in Cu-Doped β -Ga ₂ O ₃ . <i>Physical Review Letters</i> , 2022 , 128, 077402	7.4	2
166	Persistent photoconductivity in barium titanate. <i>Journal of Applied Physics</i> , 2022 , 131, 095701	2.5	1
165	Photodarkening and Dopant Segregation in Cu-doped β -Ga ₂ O ₃ Czochralski Single Crystals. <i>Journal of Crystal Growth</i> , 2021 , 126419	1.6	5
164	Photoluminescence and Raman mapping of β -Ga ₂ O ₃ . <i>AIP Advances</i> , 2021 , 11, 105006	1.5	3
163	Zn acceptors in β -Ga ₂ O ₃ crystals. <i>Journal of Applied Physics</i> , 2021 , 129, 155701	2.5	11
162	Gallium vacancy formation in oxygen annealed β -Ga ₂ O ₃ . <i>Journal of Applied Physics</i> , 2021 , 129, 245701	2.5	7
161	Classification of Semiconductors Using Photoluminescence Spectroscopy and Machine Learning. <i>Applied Spectroscopy</i> , 2021 , 37028211031618	3.1	0
160	Localized phase transition of TiO ₂ thin films induced by sub-bandgap laser irradiation. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2021 , 39, 053402	2.9	1
159	Zinc-Hydrogen and zinc-Iridium pairs in β -Ga ₂ O ₃ . <i>Applied Physics Letters</i> , 2021 , 119, 102104	3.4	4
158	Point defects in Ga ₂ O ₃ . <i>Journal of Applied Physics</i> , 2020 , 127, 101101	2.5	81
157	Confocal microscopy with a microlens array. <i>Applied Optics</i> , 2020 , 59, 3058-3063	1.7	3
156	Surface Effects on Pyrene Luminescence Excitation. <i>ACS Applied Electronic Materials</i> , 2020 , 2, 2806-28124		2
155	Enhancement of the ultraviolet photoluminescence of ZnO films: Coatings, annealing, and environmental exposure studies. <i>AIP Advances</i> , 2020 , 10, 085217	1.5	7
154	Localized UV emitters on the surface of β -Ga ₂ O ₃ . <i>Scientific Reports</i> , 2020 , 10, 21022	4.9	5
153	Insulating regions in a TiO ₂ thin film defined by laser irradiation. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2020 , 38, 032203	1.3	1
152	High Order Oxygen Local Vibrational Modes in ZnS _{1-x} O _x . <i>Physica Status Solidi (B): Basic Research</i> , 2019 , 256, 1800607	1.3	1

151	Bandgap of cubic ZnS _{1-x} O _x from optical transmission spectroscopy. <i>Journal of Applied Physics</i> , 2019 , 125, 075704	2.5	3
150	Hydrogen passivation of calcium and magnesium doped [beta]-Ga ₂ O ₃ 2019 ,		4
149	Iridium-related complexes in Czochralski-grown EGa ₂ O ₃ . <i>Journal of Applied Physics</i> , 2019 , 126, 225705	2.5	22
148	The role of hydrogen and oxygen in the persistent photoconductivity of strontium titanate. <i>Journal of Applied Physics</i> , 2018 , 123, 161545	2.5	7
147	Defects in ZnO 2018 , 1-25		4
146	Thermal stability of ultra-wide-bandgap MgZnO alloys with wurtzite structure. <i>Journal of Materials Science: Materials in Electronics</i> , 2018 , 29, 16782-16790	2.1	7
145	Compensation and hydrogen passivation of magnesium acceptors in EGa ₂ O ₃ . <i>Applied Physics Letters</i> , 2018 , 113, 052101	3.4	55
144	Oxygen vibrational modes in ZnS _{1-x} O _x alloys. <i>Journal of Applied Physics</i> , 2018 , 123, 161537	2.5	2
143	Phase-Defined van der Waals Schottky Junctions with Significantly Enhanced Thermoelectric Properties. <i>Journal of Physical Chemistry Letters</i> , 2017 , 8, 2887-2894	6.4	24
142	UV-luminescent MgZnO semiconductor alloys: nanostructure and optical properties. <i>Journal of Materials Science: Materials in Electronics</i> , 2017 , 28, 2511-2520	2.1	11
141	Formation of high concentrations of isolated Zn vacancies and evidence for their acceptor levels in ZnO. <i>Journal of Alloys and Compounds</i> , 2017 , 729, 1031-1037	5.7	17
140	Using persistent photoconductivity to write a low-resistance path in SrTiO. <i>Scientific Reports</i> , 2017 , 7, 6659	4.9	17
139	High-Pressure IR 2017 , 122-125		2
138	Achieving highly-enhanced UV photoluminescence and its origin in ZnO nanocrystalline films. <i>Optical Materials</i> , 2016 , 58, 382-389	3.3	48
137	Large persistent photoconductivity in strontium titanate single crystals 2016 ,		1
136	Modular Scanning Confocal Microscope with Digital Image Processing. <i>PLoS ONE</i> , 2016 , 11, e0166212	3.7	4
135	Tutorial: Defects in semiconductors—Combining experiment and theory. <i>Journal of Applied Physics</i> , 2016 , 119, 181101	2.5	206
134	Hydrogen-related complexes in Li-diffused ZnO single crystals. <i>Journal of Applied Physics</i> , 2016 , 120, 035703	2.5	11

133	Spectroscopic studies of the mechanism of reversible photodegradation of 1-substituted aminoanthraquinone-doped polymers. <i>Journal of Chemical Physics</i> , 2016 , 144, 114902	3.9	14
132	High pressure Γ_0 - Γ_1 phase transition in bulk and nanocrystalline In ₂ Se ₃ . <i>High Pressure Research</i> , 2016 , 36, 549-556	1.6	2
131	Point Defects in ZnO. <i>Semiconductors and Semimetals</i> , 2015 , 91, 279-313	0.6	17
130	Acceptors in ZnO. <i>Journal of Applied Physics</i> , 2015 , 117, 112802	2.5	45
129	Phonon dynamics and Urbach energy studies of MgZnO alloys. <i>Journal of Applied Physics</i> , 2015 , 117, 125702	2.0	26
128	Large Persistent Photoconductivity in Strontium Titanate at Room Temperature. <i>Materials Research Society Symposia Proceedings</i> , 2015 , 1792, 1		5
127	Electronic transport in molybdenum dioxide thin films. <i>Journal of Materials Science: Materials in Electronics</i> , 2015 , 26, 9717-9720	2.1	5
126	P-type conductivity in annealed strontium titanate. <i>AIP Advances</i> , 2015 , 5, 127217	1.5	7
125	Potassium acceptor doping of ZnO crystals. <i>AIP Advances</i> , 2015 , 5, 057107	1.5	8
124	Confocal microscopy of fluids under static pressure. <i>Journal of Physics: Conference Series</i> , 2014 , 500, 142020	2.0	20
123	Defects and persistent conductivity in SrTiO ₃ 2014 ,		2
122	Evidence for a shallow Cu acceptor in Si from infrared spectroscopy and photoconductivity. <i>Physical Review B</i> , 2014 , 90,	3.3	2
121	Recharging behavior of nitrogen-centers in ZnO. <i>Journal of Applied Physics</i> , 2014 , 116, 063701	2.5	9
120	Persistent Photoconductivity in Bulk Strontium Titanate. <i>Materials Research Society Symposia Proceedings</i> , 2014 , 1675, 87-91		
119	Persistent photoconductivity in strontium titanate. <i>Physical Review Letters</i> , 2013 , 111, 187403	7.4	104
118	Anharmonic resonant Raman modes in Mg _{0.2} Zn _{0.8} O. <i>Physical Review B</i> , 2013 , 87,	3.3	7
117	Vibrational Spectroscopy of Na ⁺ Complexes in ZnO. <i>Journal of Electronic Materials</i> , 2013 , 42, 3426-3428	1.9	16
116	Positron lifetime measurements of hydrogen passivation of cation vacancies in yttrium aluminum oxide garnets. <i>Physical Review B</i> , 2013 , 88,	3.3	36

115	Nitrogen and vacancy clusters in ZnO. <i>Journal of Materials Research</i> , 2013 , 28, 1977-1983	2.5	27
114	Formation of isolated Zn vacancies in ZnO single crystals by absorption of ultraviolet radiation: a combined study using positron annihilation, photoluminescence, and mass spectroscopy. <i>Physical Review Letters</i> , 2013 , 111, 017401	7.4	61
113	Pressure-induced phase transformation of In ₂ Se ₃ . <i>Applied Physics Letters</i> , 2013 , 102, 062105	3.4	39
112	Use of dynamic compression to probe semiconductor response at large strains. <i>Physica Status Solidi (B): Basic Research</i> , 2013 , 250, 683-687	1.3	2
111	High pressure-high temperature decomposition of β-cyclotrimethylene trinitramine. <i>Journal of Physical Chemistry A</i> , 2012 , 116, 9680-8	2.8	23
110	Hydrogen in oxide semiconductors. <i>Journal of Materials Research</i> , 2012 , 27, 2190-2198	2.5	52
109	Compensation of Acceptors in ZnO Nanocrystals by Adsorption of Formic Acid. <i>Journal of Physical Chemistry C</i> , 2012 , 116, 17248-17251	3.8	13
108	Optical Properties of ZnO-Alloyed Nanocrystalline Films. <i>Journal of Nanomaterials</i> , 2012 , 2012, 1-7	3.2	16
107	Zn _{Sx} O _{1-x} Films Grown on Flexible Substrates. <i>Materials Research Society Symposia Proceedings</i> , 2012 , 1394, 48		1
106	Acceptor Dopants in Bulk and Nanoscale ZnO. <i>Materials Research Society Symposia Proceedings</i> , 2012 , 1494, 3-12		
105	Nitrogen is a deep acceptor in ZnO. <i>AIP Advances</i> , 2011 , 1, 022105	1.5	116
104	Order-of-magnitude reduction of carrier lifetimes in [100] n-type GaAs shock-compressed to 4 GPa. <i>Applied Physics Letters</i> , 2011 , 98, 092107	3.4	5
103	Cu-doping of ZnO by nuclear transmutation. <i>Applied Physics Letters</i> , 2011 , 99, 202109	3.4	20
102	Acceptors in ZnO nanocrystals. <i>Applied Physics Letters</i> , 2011 , 98, 232112	3.4	28
101	Infrared absorption of hydrogen-related defects in strontium titanate. <i>Journal of Applied Physics</i> , 2011 , 109, 063706	2.5	25
100	Equations of state for ZnO and MgZnO by high pressure x-ray diffraction. <i>Journal of Applied Physics</i> , 2011 , 110, 073511	2.5	11
99	Acceptor and surface states of ZnO nanocrystals: a unified model. <i>Nanotechnology</i> , 2011 , 22, 475703	3.4	20
98	Experimental Evidence for Nitrogen as a Deep Acceptor in ZnO. <i>Materials Research Society Symposia Proceedings</i> , 2011 , 1394, 21		1

97	Structure and stability of NH complexes in single-crystal ZnO. <i>Journal of Applied Physics</i> , 2010 , 107, 11353-6		11
96	Incorporation of Cu acceptors in ZnO nanocrystals. <i>Journal of Applied Physics</i> , 2010 , 108, 064301	2.5	12
95	Equation of state and refractive index of argon at high pressure by confocal microscopy. <i>Physical Review B</i> , 2010 , 81,	3.3	8
94	Hydrogen donors in SnO ₂ studied by infrared spectroscopy and first-principles calculations. <i>Physical Review B</i> , 2010 , 82,	3.3	41
93	Bound exciton luminescence in shock compressed GaP:S and GaP:N. <i>Journal of Applied Physics</i> , 2009 , 106, 023710	2.5	1
92	Real-time band structure changes of GaAs during continuous dynamic compression to 5 GPa. <i>Applied Physics Letters</i> , 2009 , 95, 152108	3.4	3
91	Transformation of GaAs into an indirect L-band-gap semiconductor under uniaxial strain. <i>Physical Review B</i> , 2009 , 80,	3.3	16
90	Suppression of conductivity in Mn-doped ZnO thin films. <i>Journal of Applied Physics</i> , 2009 , 105, 013715	2.5	37
89	Resonant interaction between hydrogen vibrational modes in AlSb:Se. <i>Physical Review Letters</i> , 2009 , 102, 135502	7.4	6
88	Hydrogen-related defects in bulk ZnO. <i>Materials Research Society Symposia Proceedings</i> , 2009 , 1167, 7		
87	Dopants in nanoscale ZnO. <i>Materials Research Society Symposia Proceedings</i> , 2009 , 1174, 110		
86	Nitrogen and hydrogen in bulk single-crystal ZnO. <i>Physica B: Condensed Matter</i> , 2009 , 404, 4810-4812	2.8	6
85	Defects in ZnO. <i>Journal of Applied Physics</i> , 2009 , 106, 071101	2.5	855
84	Measuring the volume of a fluid in a diamond anvil cell using a confocal microscope. <i>Applied Optics</i> , 2009 , 48, 1758-63	0.2	5
83	Optical transitions and multiphonon Raman scattering of Cu doped ZnO and MgZnO ceramics. <i>Applied Physics Letters</i> , 2009 , 94, 061919	3.4	18
82	X-ray diffraction of Mg _x Zn _{1-x} O and ZnO nanocrystals under high pressure. <i>Journal of Applied Physics</i> , 2009 , 106, 013511	2.5	15
81	Action potential propagation imaged with high temporal resolution near-infrared video microscopy and polarized light. <i>NeuroImage</i> , 2008 , 40, 1034-43	7.9	20
80	Strong Fano resonance of oxygen-hydrogen bonds on oblique angle deposited Mg nanoblades. <i>Applied Physics Letters</i> , 2008 , 92, 183112	3.4	2

79	Band-gap luminescence of GaP:S shock compressed to 5GPa. <i>Applied Physics Letters</i> , 2008 , 92, 142104	3.4	6
78	Unambiguous identification of nitrogen-hydrogen complexes in ZnO. <i>Physical Review B</i> , 2007 , 76,	3.3	42
77	Infrared and Raman spectroscopy of ZnO nanoparticles annealed in hydrogen. <i>Journal of Applied Physics</i> , 2007 , 102, 043529	2.5	22
76	Sources of n-type conductivity in ZnO. <i>Physica B: Condensed Matter</i> , 2007 , 401-402, 355-357	2.8	54
75	Hydrogen complexes in ZnO grown by chemical vapor transport. <i>Physica B: Condensed Matter</i> , 2007 , 401-402, 395-398	2.8	9
74	Indirect band-gap transitions in GaP shocked along the [100], [110], and [111] axes. <i>Physical Review B</i> , 2007 , 75,	3.3	7
73	Recording invertebrate nerve activation with modulated light changes. <i>Applied Optics</i> , 2007 , 46, 1866-711.7	1.7	3
72	Pressure response of the ultraviolet photoluminescence of ZnO and MgZnO nanocrystallites. <i>Applied Physics Letters</i> , 2006 , 89, 171909	3.4	28
71	Hydrogen in bulk and nanoscale ZnO. <i>Physica B: Condensed Matter</i> , 2006 , 376-377, 690-693	2.8	19
70	Infrared spectroscopy of ZnO nanoparticles containing CO ₂ impurities. <i>Applied Physics Letters</i> , 2005 , 86, 073111	3.4	45
69	Infrared Spectroscopy of Impurities in ZnO Nanoparticles. <i>Materials Research Society Symposia Proceedings</i> , 2005 , 864, 4401		1
68	Hydrogen Donors in ZnO. <i>Materials Research Society Symposia Proceedings</i> , 2005 , 864, 1041		4
67	Structure and stability of OH donors in ZnO from high-pressure and infrared spectroscopy. <i>Physical Review B</i> , 2005 , 72,	3.3	98
66	Hydrogen Donors in Zinc Oxide 2005 , 125-132		2
65	Shock-induced band-gap shift in GaN: Anisotropy of the deformation potentials. <i>Physical Review B</i> , 2005 , 71,	3.3	33
64	Ferromagnetism in Ga(1-x)Mn(x)P: evidence for inter-Mn exchange mediated by localized holes within a detached impurity band. <i>Physical Review Letters</i> , 2005 , 95, 207204	7.4	87
63	Isotope effects in the electronic spectrum of S ⁺ and Se ⁺ in silicon. <i>Physical Review B</i> , 2004 , 69,	3.3	9
62	Conformation of p-terphenyl under hydrostatic pressure. <i>Journal of Chemical Physics</i> , 2004 , 120, 1841-5	3.9	25

61	VIBRATIONAL STUDIES AND RESONANT INTERACTION BETWEEN LOCALIZED AND EXTENDED MODES IN Si:O UNDER PRESSURE. <i>Modern Physics Letters B</i> , 2004 , 18, 1013-1028	1.6	1
60	Pressure tuning of localized and extended vibrational modes in Si:O. <i>Physica Status Solidi (B): Basic Research</i> , 2004 , 241, 3300-3305	1.3	2
59	Isotope effects in the electronic spectra of singly ionised S ⁺ and Se ⁺ donors in silicon. <i>Physica B: Condensed Matter</i> , 2003 , 340-342, 760-764	2.8	
58	Infrared spectroscopy of hydrogen in annealed zinc oxide. <i>Physica B: Condensed Matter</i> , 2003 , 340-342, 221-224	2.8	37
57	Interaction between localized and extended modes of oxygen in silicon. <i>Physica B: Condensed Matter</i> , 2003 , 340-342, 514-517	2.8	2
56	The Franz-Keldysh effect in shocked GaN:Mg. <i>Applied Physics Letters</i> , 2003 , 82, 2085-2087	3.4	12
55	Resonant interaction between localized and extended vibrational modes in Si: 18O under pressure. <i>Physical Review Letters</i> , 2003 , 90, 095505	7.4	11
54	Pressure dependence of donor excitation spectra in AlSb. <i>Physical Review B</i> , 2003 , 67,	3.3	2
53	Effect of composition on the band gap of strained In _x Ga _{1-x} N alloys. <i>Journal of Applied Physics</i> , 2003 , 93, 4340-4342	2.5	54
52	Infrared spectroscopy of biphenyl under hydrostatic pressure. <i>Journal of Chemical Physics</i> , 2002 , 117, 3748-3752	3.9	24
51	Band gap changes of GaN shocked to 13 GPa. <i>Applied Physics Letters</i> , 2002 , 80, 1912-1914	3.4	8
50	N ₂ and CO ₂ vibrational modes in solid nitrogen under pressure. <i>Journal of Chemical Physics</i> , 2002 , 116, 1607-1612	3.9	9
49	Infrared Spectroscopy of Bis(4-nitrophenyl) Disulfide Grown on a Pb Layer. <i>Chemistry Letters</i> , 2002 , 31, 1138-1139	1.7	3
48	Infrared spectroscopy of hydrogen in ZnO. <i>Applied Physics Letters</i> , 2002 , 81, 3807-3809	3.4	178
47	Acceptor-Hydrogen complexes in semiconductors under pressure. <i>Physica B: Condensed Matter</i> , 2001 , 308-310, 780-783	2.8	1
46	Carbon acceptors and carbon-hydrogen complexes in AlSb. <i>Physical Review B</i> , 2001 , 65,	3.3	23
45	Flattening of organic molecules under pressure. <i>Journal of Chemical Physics</i> , 2001 , 114, 5465-5467	3.9	21
44	Pressure dependence of local vibrational modes in InP. <i>Physical Review B</i> , 2001 , 63,	3.3	9

43	Band Gap Shift of GaN under Uniaxial Strain Compression. <i>Materials Research Society Symposia Proceedings</i> , 2001 , 693, 242		1
42	Local vibrational modes of impurities in semiconductors. <i>Journal of Applied Physics</i> , 2000 , 87, 3593-3617	2.5	109
41	Doping of AlGa _N Alloys. <i>MRS Internet Journal of Nitride Semiconductor Research</i> , 1999 , 4, 890-901		20
40	Phase separation in InGa _N multiple quantum wells annealed at high nitrogen pressures. <i>Applied Physics Letters</i> , 1999 , 75, 3950-3952	3.4	36
39	Shallow to deep transformation of Se donors in GaSb under hydrostatic pressure. <i>Physical Review B</i> , 1999 , 59, 8003-8007	3.3	1
38	Hydrogen in compound semiconductors. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1999 , 17, 2188-2193	2.9	9
37	DX CENTERS IN AlGa _N . <i>International Journal of Modern Physics B</i> , 1999 , 13, 1363-1378	1.1	7
36	Hydrogen in III-V and II-VI Semiconductors. <i>Semiconductors and Semimetals</i> , 1999 , 373-440	0.6	4
35	Large and composition-dependent band gap bowing in In _x Ga _{1-x} N alloys. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1999 , 59, 274-278	3.1	55
34	MOCVD growth and characterization of AlGaInN multiple quantum well heterostructures and laser diodes. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1999 , 59, 33-38	3.1	1
33	Phase separation in annealed InGa _N /Ga _N multiple quantum wells. <i>Journal of Crystal Growth</i> , 1998 , 189-190, 33-36	1.6	16
32	Anti-crossing behavior of local vibrational modes in AlSb. <i>Solid State Communications</i> , 1998 , 106, 587-590	1.6	12
31	Characteristics of InGa _N -AlGa _N multiple-quantum-well laser diodes. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 1998 , 4, 498-504	3.8	18
30	Pressure dependence of optical transitions in In _{0.15} Ga _{0.85} N/Ga _N multiple quantum wells. <i>Physical Review B</i> , 1998 , 58, R10191-R10194	3.3	17
29	Optical properties of In _x Ga _{1-x} N alloys grown by metalorganic chemical vapor deposition. <i>Journal of Applied Physics</i> , 1998 , 84, 4452-4458	2.5	127
28	Large band gap bowing of In _x Ga _{1-x} N alloys. <i>Applied Physics Letters</i> , 1998 , 72, 2725-2726	3.4	187
27	Phase separation in InGa _N /Ga _N multiple quantum wells. <i>Applied Physics Letters</i> , 1998 , 72, 1730-1732	3.4	176
26	Structural and optical properties of epitaxially overgrown third-order gratings for InGa _N /Ga _N -based distributed feedback lasers. <i>Applied Physics Letters</i> , 1998 , 73, 2706-2708	3.4	6

25	Structural and optical properties of pseudomorphic In _x Ga _{1-x} N alloys. <i>Applied Physics Letters</i> , 1998 , 73, 1757-1759	3-4	55
24	Comparison study of photoluminescence from InGaN/GaN multiple quantum wells and InGaN epitaxial layers under large hydrostatic pressure. <i>Applied Physics Letters</i> , 1998 , 73, 1613-1615	3-4	9
23	Interdiffusion of In and Ga in InGaN quantum wells. <i>Applied Physics Letters</i> , 1998 , 73, 1281-1283	3-4	66
22	Metastability of Oxygen Donors in AlGaIn. <i>Physical Review Letters</i> , 1998 , 80, 4008-4011	7-4	138
21	Doping of AlGaIn Alloys. <i>Materials Research Society Symposia Proceedings</i> , 1998 , 537, 1		4
20	Evidence for Oxygen DX Centers in AlGaIn. <i>Materials Research Society Symposia Proceedings</i> , 1998 , 512, 531		1
19	Hydrogen Local Vibrational Modes in Compound Semiconductors. <i>Materials Research Society Symposia Proceedings</i> , 1998 , 513, 217		2
18	Pressure Dependence of Optical Transitions in InGaIn/GaN Multiple Quantum Wells. <i>Materials Research Society Symposia Proceedings</i> , 1998 , 537, 1		
17	Disordering of InGaIn/GaN Superlattices After High-Pressure Annealing. <i>Materials Research Society Symposia Proceedings</i> , 1998 , 537, 1		
16	Interstitial oxygen in silicon under hydrostatic pressure. <i>Physical Review B</i> , 1997 , 56, 9520-9523	3-3	19
15	Local vibrational modes in GaAs under hydrostatic pressure. <i>Physical Review B</i> , 1997 , 56, 6404-6407	3-3	19
14	Resonant Interaction Between Local Vibrational Modes and Extended Lattice Phonons in AlSb. <i>Materials Science Forum</i> , 1997 , 258-263, 1247-1252	0-4	3
13	Infrared Optical Studies of Semiconductors at Large Hydrostatic Pressures. <i>Materials Research Society Symposia Proceedings</i> , 1997 , 499, 371		
12	Spectroscopic Identification of the Acceptor-Hydrogen Complex in Mg-Doped GaN Grown by MOCVD. <i>Materials Research Society Symposia Proceedings</i> , 1997 , 468, 117		0
11	Phase Separation in InGaIn/GaN Multiple Quantum Wells. <i>Materials Research Society Symposia Proceedings</i> , 1997 , 482, 981		2
10	Local vibrational modes of the MgIn acceptor complex in GaN. <i>Applied Physics Letters</i> , 1996 , 69, 3725-3727	3-4	169
9	Vibrational spectroscopy of arsenic-hydrogen complexes in ZnSe. <i>Applied Physics Letters</i> , 1996 , 68, 3476-3478	3-4	12
8	Infrared absorption of solid nitrogen at high pressures. <i>Physical Review B</i> , 1996 , 54, 8962-8964	3-3	33

7	Hydrogen passivation of Se and Te in AlSb. <i>Physical Review B</i> , 1996 , 53, 16297-16301	3.3	16
6	Fano interference of the Raman phonon in heavily boron-doped diamond films grown by chemical vapor deposition. <i>Applied Physics Letters</i> , 1995 , 66, 616-618	3.4	161
5	Vibrational spectroscopy of group-II-acceptor-hydrogen complexes in GaP. <i>Physical Review B</i> , 1995 , 52, 11859-11864	3.3	17
4	Spectroscopy of hydrogen-related complexes in GaP:Zn. <i>Applied Physics Letters</i> , 1994 , 65, 2191-2192	3.4	13
3	Matrix reactions of P4 and P2 with O3 molecules. <i>Journal of Molecular Structure</i> , 1990 , 222, 95-108	3.4	22
2	Dopants and Defects in Semiconductors		51
1	Dopants and Defects in Semiconductors		16